# P-Channel 100-V (D-S) MOSFET

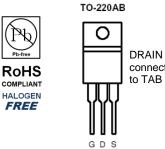
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

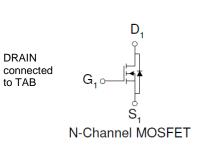
# **Typical Applications:**

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
-100	38 @ V <sub>GS</sub> = -10V	-80ª	
	43 @ V <sub>GS</sub> = -5.5V	-80	



Top View



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			-100	V	
Gate-Source Voltage		$V_{GS}$	±20	v	
Continuous Drain Current a	T <sub>C</sub> =25°C	$I_D$	-80	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-320		
Continuous Source Current (Diode Conduction) <sup>a</sup>			110	Α	
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	300	W	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

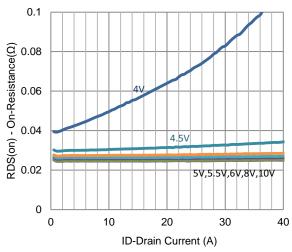
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25		
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	120			Α	
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$			38	mΩ	
	r <sub>DS(on)</sub>	$V_{GS} = -5.5 \text{ V}, I_{D} = -36 \text{ A}$			43		
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -20 \text{ A}$		30		S	
Diode Forward Voltage	$V_{SD}$	$I_{S} = -55 \text{ A}, V_{GS} = 0 \text{ V}$		-0.91		V	
		Dynamic					
Total Gate Charge	$Q_g$	$V_{DS} = -50 \text{ V}, V_{GS} = -5.5 \text{ V},$		164		nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -3.3 \text{ V},$ $I_{D} = -20 \text{ A}$		51			
Gate-Drain Charge	$Q_gd$	1D = 20 A		77			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -50 \text{ V}, R_1 = 2.5 \Omega,$		26		ns	
Rise Time	t <sub>r</sub>	$V_{DS} = -30 \text{ V}, K_L - 2.3 \Omega,$ $I_D = -20 \text{ A},$		65			
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		266			
Fall Time	t <sub>f</sub>	V GEN - 10 V, T GEN - 0 12		111			
Input Capacitance	C <sub>iss</sub>			15378			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		774		pF	
Reverse Transfer Capacitance	$C_{rss}$			530			

#### **Notes**

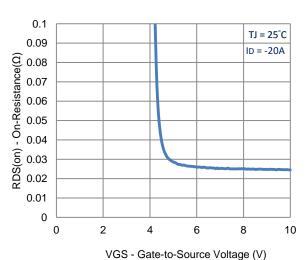
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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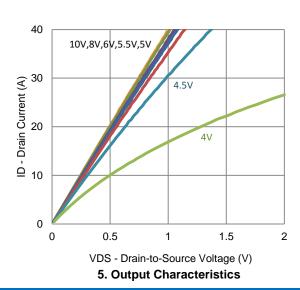
## **Typical Electrical Characteristics**

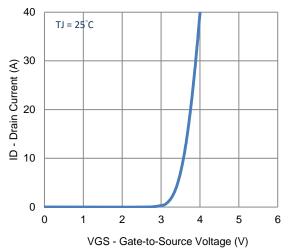


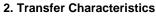
#### 1. On-Resistance vs. Drain Current

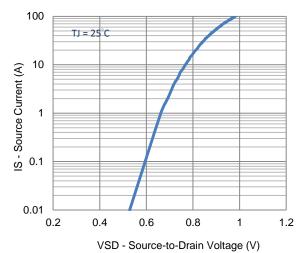


3. On-Resistance vs. Gate-to-Source Voltage

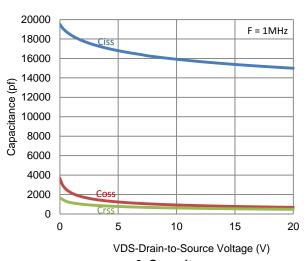




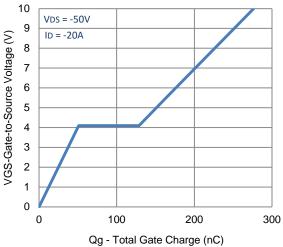


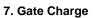


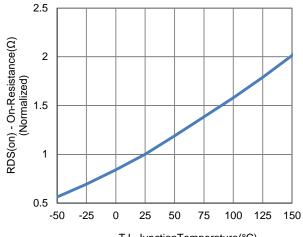
4. Drain-to-Source Forward Voltage



## **Typical Electrical Characteristics**

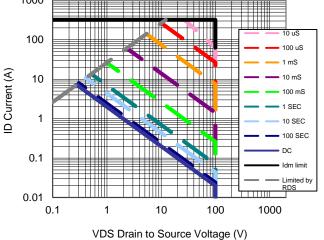




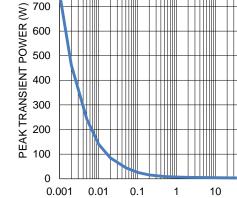


TJ -JunctionTemperature(°C)

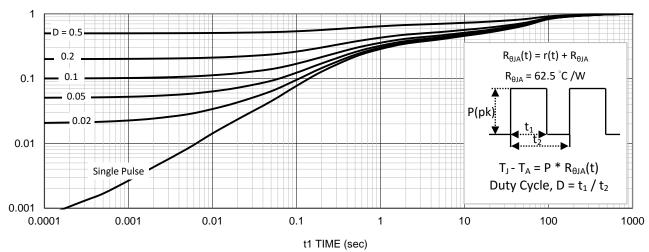




9. Safe Operating Area



t1 TIME (SEC) 10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

1000

100

# **Package Information**

